Features:

- ☐ Low Intrinsic Capacitances.
- ☐ Excellent Switching Characteristics.
- ☐ Extended Safe Operating Area.
- ☐ Unrivalled Gate Charge :Qg= 155nC (Typ.).
- ☐ BVDSS=100V,I_D=180A
- ☐ R_{DS}(on) : 5mΩ (Max) @V_G=10V
- ☐ 100% Avalanche Tested

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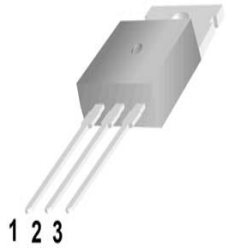
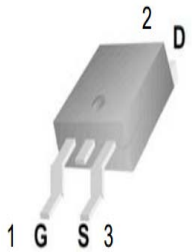
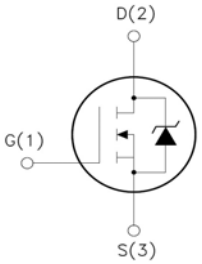


T0-263





1.Gate (G)
2.Drain (D)
3.Source (S)

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Symbol	Parameter		Maximum	Unit
V_{DSS}	Drain-to-Source Voltage		100	V
V_{GSS}	Gate-to-Source Voltage		±25	V
I_D[3]	Continuous Drain Current	T_C=25°C	180	A
		T_C=100°C	140	
I_{DP}[4]	Pulsed Drain Current	T_C=25°C	600	
IAS[5]	Avalanche Current		40	
EAS[5]	Avalanche energy		700	mJ
PD	Maximum Power Dissipation	T_C=25°C	240	W
		T_C=100°C	125	
T_J, T_{STG}	Junction & Storage Temperature Range		-55~175	°C

Thermal Characteristics

Symbol	Parameter	Typical	Unit
Rθjc	Thermal Resistance-Junction to Case	0.6	℃/W
Rθja	Thermal Resistance-Junction to Ambient	62.5	

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Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250uA	100	—	—	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V,V_{GS}=0V	—	—	1	uA
		T_J=125°C	—	—	100	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250uA	2	3	4	V
I_{GSS}	Gate Leakage Current	V_{GS}=±25V, V_{DS}=0V	—	—	±100	nA
$R_{DS(on)}$[1]	Drain-Source On-Resistance	V_{GS}=10V, I_D=40A	—	4.5	5	mΩ
			—	—	—	
Diode Characteristics						
V_{SD}[1]	Diode Forward Voltage	I_{SD}=40A,V_{GS}=0V	—	0.8	1.3	V
I_S[3]	Diode Continuous Forward Current		—	—	180	A
t_{rr}	Reverse Recovery Time	I_F=40A, dI/dt=100A/us	—	65	—	nS
Q_{rr}	Reverse Recovery Charge		—	103	—	nC
Dynamic Characteristics[2]						
R_G	Gate Resistance	V_{GS}=0V, V_{DS}=0V, Frequency=1MHz	—	2.5	—	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V Frequency=1MHz	—	7850	—	pF
C_{oss}	Output Capacitance		—	1010	—	
C_{rss}	Reverse Transfer Capacitance		—	630	—	
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=37.5V,I_D=40A, V_{GS}=10V,R_G=6.8Ω	—	28	—	nS
t_r	Rise Time		—	45	—	
$t_{d(off)}$	Turn-Off Delay Time		—	84	—	
t_f	Fall Time		—	49	—	
Gate Charge Characteristics[2]						
Q_g	Total Gate Charge	V_{DS}=37.5V,V_{GS}=10V I_D=40A	—	184	—	nC
Q_{gs}	Gate-to-Source Charge		—	33	—	
Q_{gd}	Gate-to-Drain Charge		—	60	—	

Note: 1: Pulse test; pulse width ≦ 300us, duty cycle ≦ 2%.
2: Guaranteed by design, not subject to production testing.
3: Package limitation current is 50A.Calculated continuous current based on maximum allowable junction temperature.
4: Repetitive rating, pulse width limited by max junction temperature.
5: Starting TJ = 25°C,L = 0.5mH, VDD=80V, IAS = 74A.

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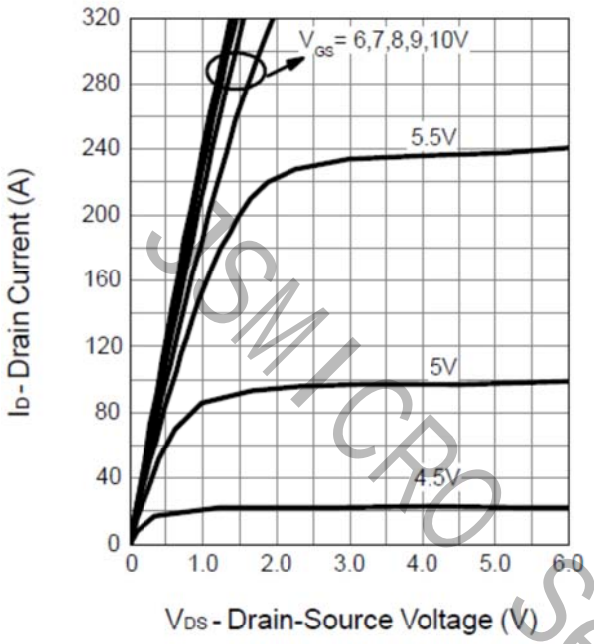
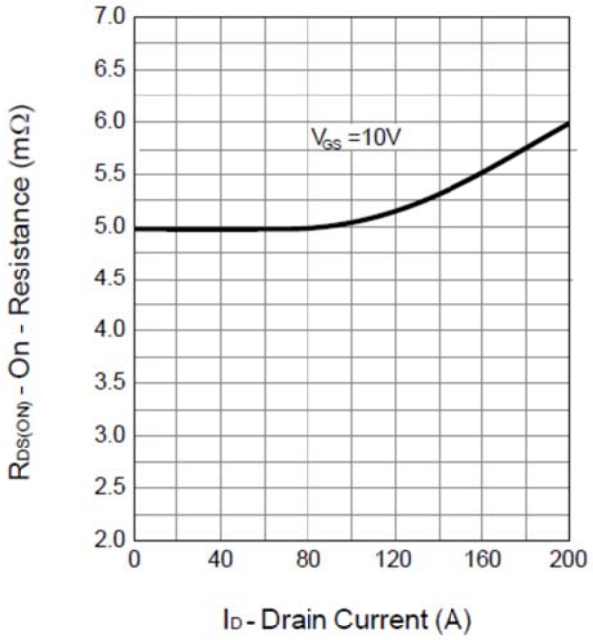
Typical Characteristics

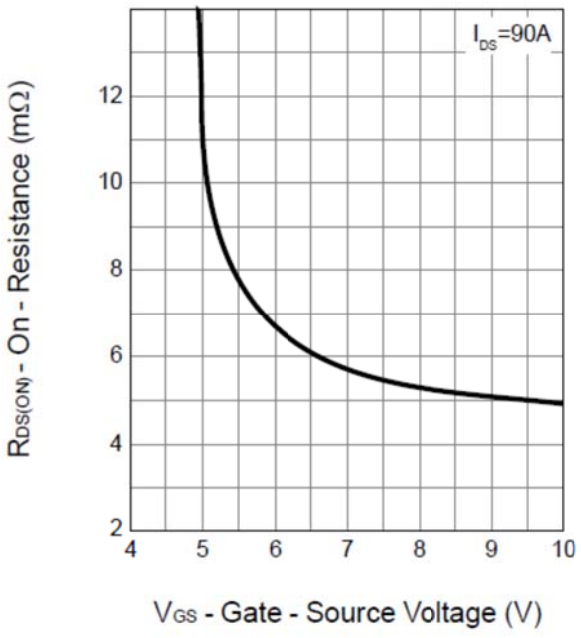
Output Characteristics



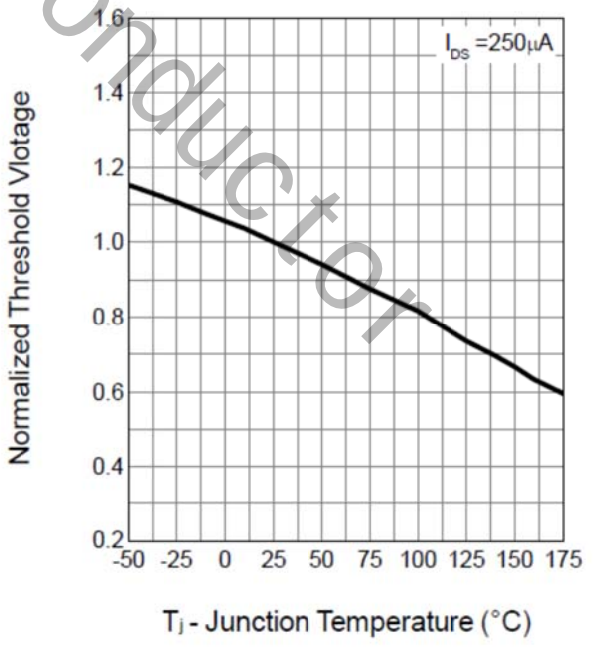
Drain-Source On Resistance



Drain-Source On Resistance



Gate Threshold Voltage



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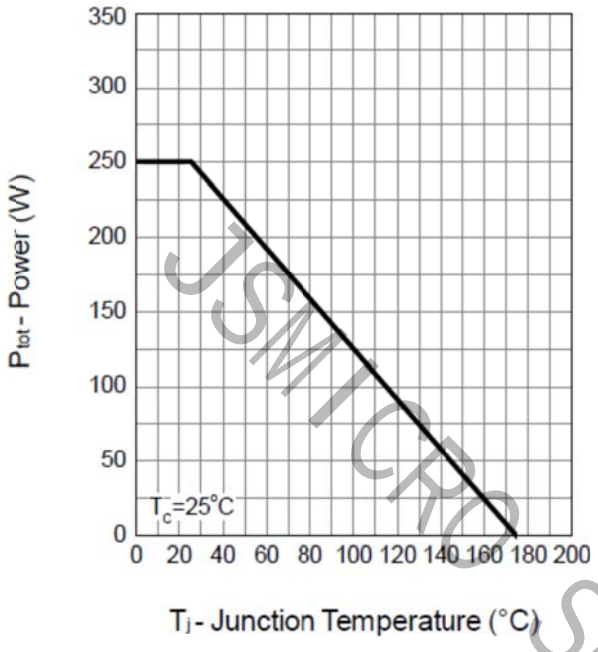
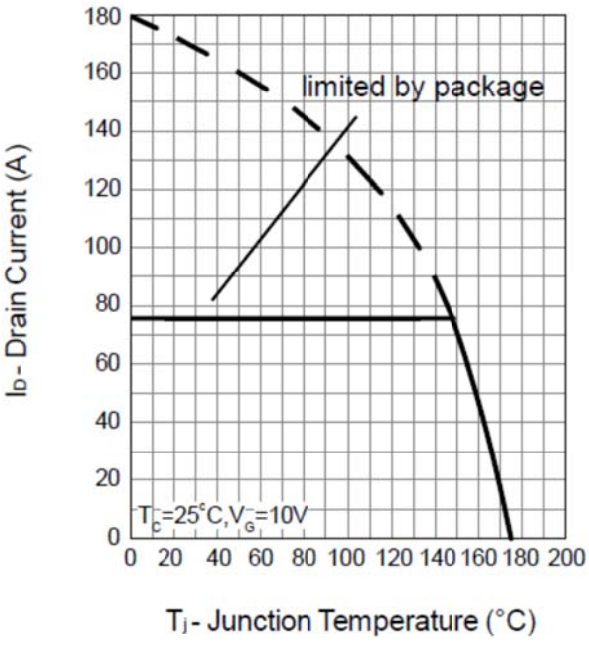
Typical Characteristics (Continued)

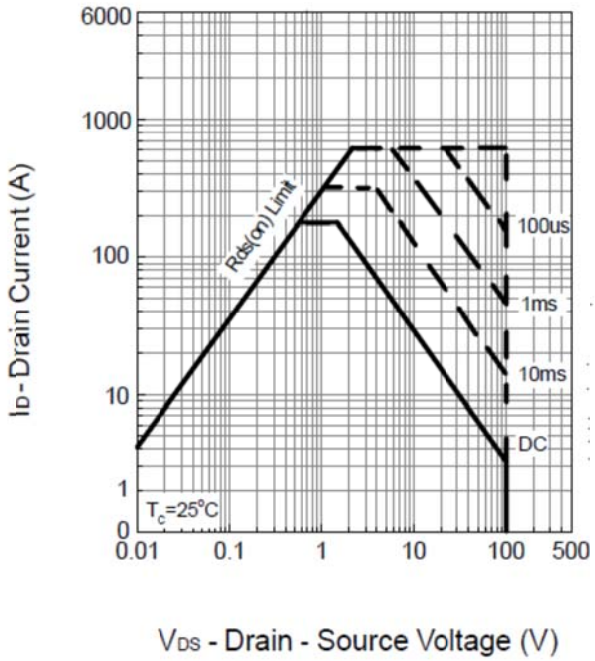
Power Dissipation



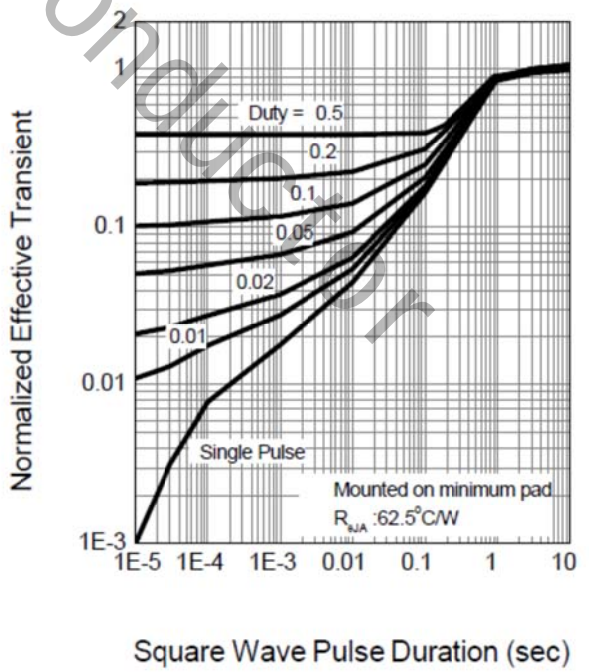
Drain Current



Safe Operation Area



Thermal Transient Impedance



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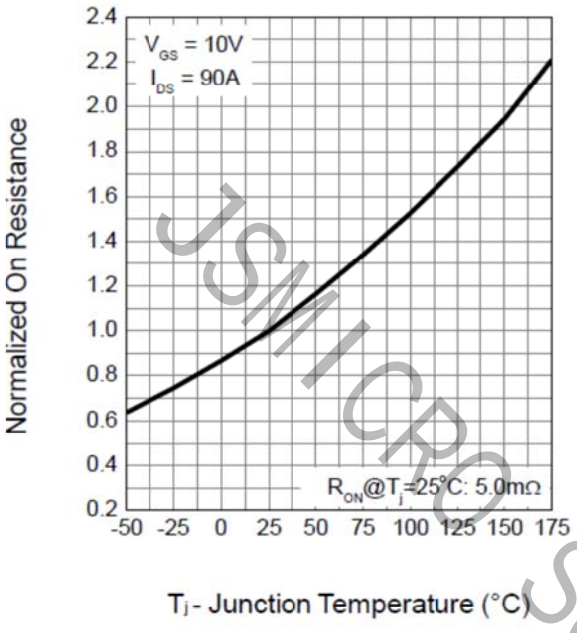
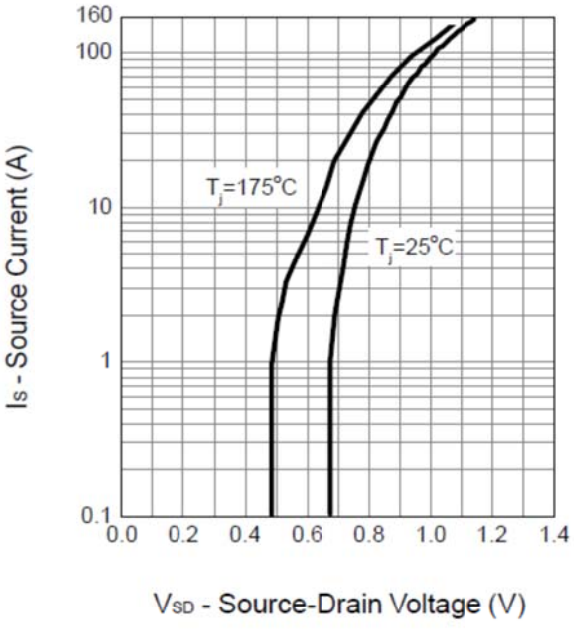
Typical Characteristics (Continued)

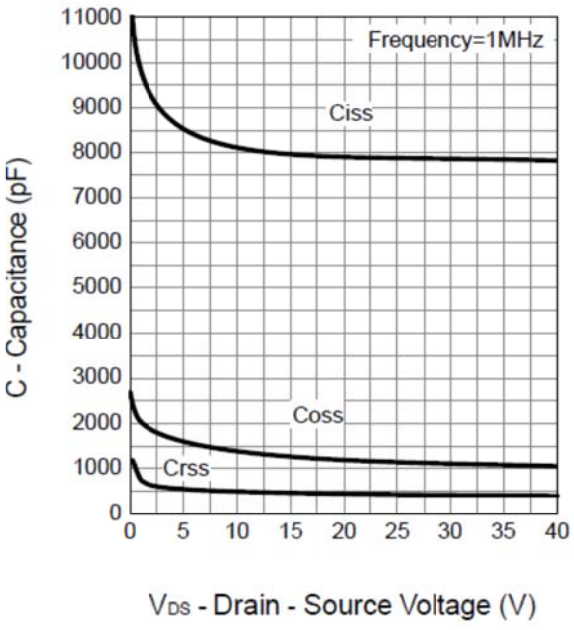
Drain-Source On Resistance



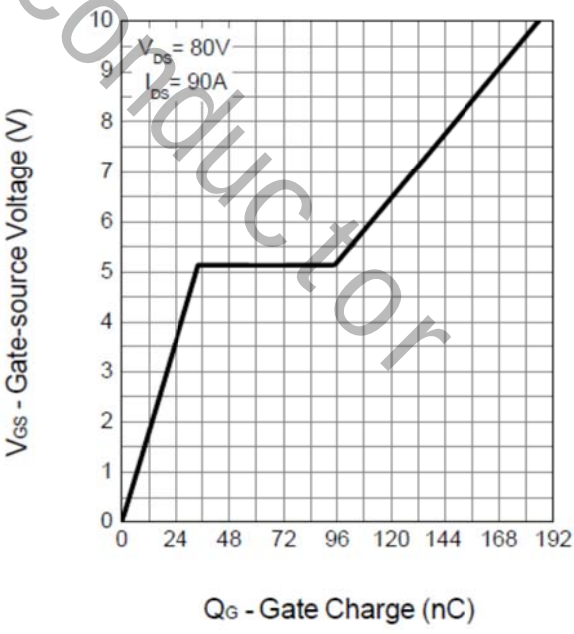
Source-Drain Diode Forward



Capacitance



Gate Charge



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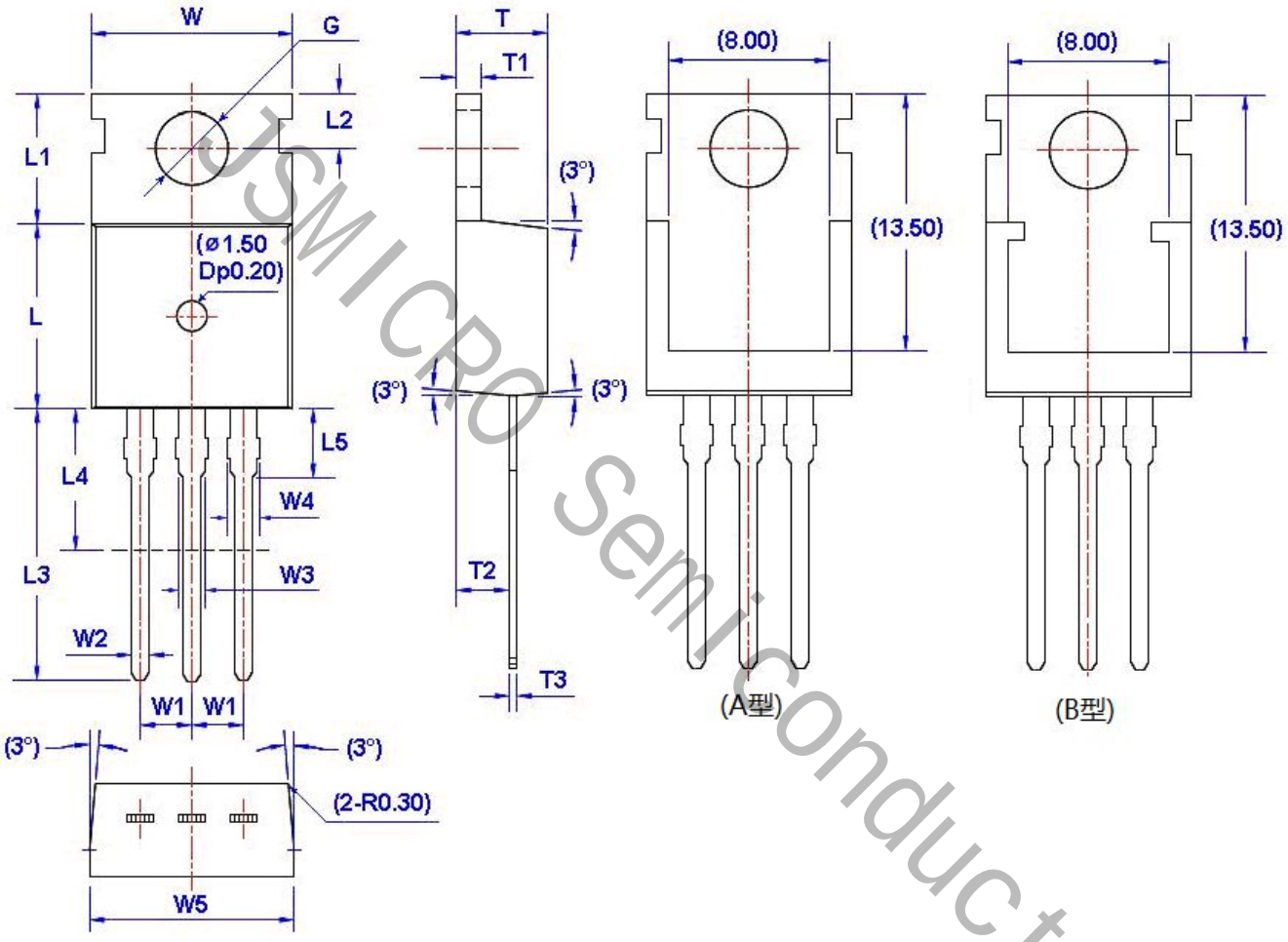
Package Dimension

TO-220

Unit:mm



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Symbol	Size		Symbol	Size		Symbol	Size		Symbol	Size	
	Min	Max		Min	Max		Min	Max		Min	Max
W	9.66	10.28	W5	9.80	10.20	L4**	6.20	6.60	T3	0.45	0.60
W1	2.54（TYP）		L	9.00	9.40	L5	2.79	3.30	G(Φ)	3.50	3.70
W2	0.70	0.95	L1	6.40	6.80	T	4.30	4.70			
W3	1.17	1.37	L2	2.70	2.90	T1	1.15	1.40			
W4*	1.32	1.72	L3	12.70	14.27	T2	2.20	2.60			